

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



528 765

(43) International Publication Date
8 April 2004 (08.04.2004)

PCT

(10) International Publication Number
WO 2004/030060 A1

(51) International Patent Classification⁷: **H01L 21/22**

[CN/SG]; BLK 722 Pasir Ris St. 72, #02-123, 510722 Singapore (SG). **OW**, Boon-Koon [SG/SG]; BLK 221 Pasir Ris St. 21, #11-108, 510221 Singapore (SG).

(21) International Application Number:
PCT/EP2003/010410

(22) International Filing Date:
18 September 2003 (18.09.2003)

(74) Agents: **STAUDACHER, Wolfgang** et al.; WACKER-CHEMIE GMBH, Hanns-Seidel-Platz 4, 81737 München (DE).

(25) Filing Language: English

(81) Designated States (*national*): CN, JP, KR, US.

(26) Publication Language: English

(84) Designated States (*regional*): European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR).

(30) Priority Data:
200205833-7 25 September 2002 (25.09.2002) SG

(71) Applicant (*for all designated States except US*):
WACKER SILTRONIC AG [DE/DE]; Johannes-Hess-Strasse 24, 84489 Burghausen (DE).

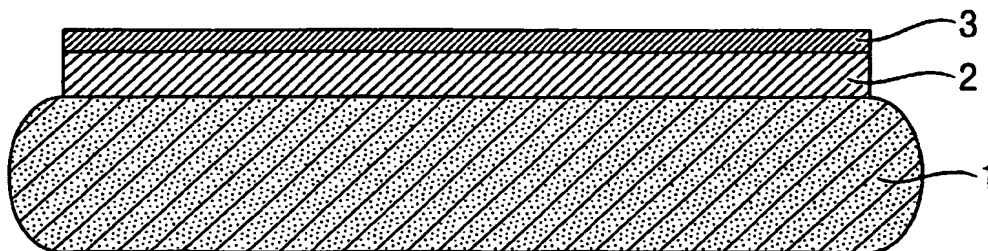
Published:
— with international search report

(72) Inventors; and

(75) Inventors/Applicants (*for US only*): **LI, Jin-Xing**

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: TWO LAYER LTO TEMPERATURE OXIDE BACKSIDE SEAL FOR A WAFER



(57) Abstract: A two layer LTO backside seal for a wafer. The two layer LTO backside seal includes a low stress LTO layer having a first major side and a second major side, the first major side of the low stress LTO layer adjacent to one major side of the wafer. The two layer LTO backside seal further includes a high stress LTO layer having a first major side and second major side, the first major side of the high stress LTO layer adjacent the second major side of the low stress LTO layer.

WO 2004/030060 A1